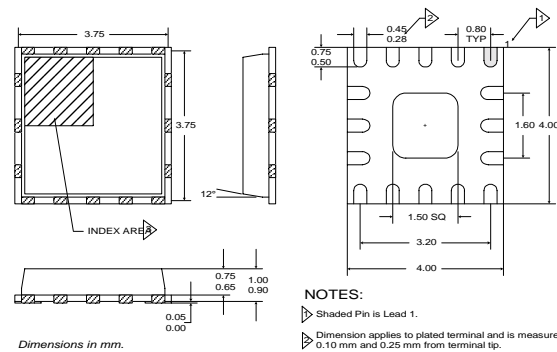


Typical Applications

- 3V 1850-1910MHz CDMA-2000 Handsets
- Commercial and Consumer Systems
- 3V 1920-1980MHz W-CDMA Handsets
- Portable Battery-Powered Equipment
- Spread-Spectrum Systems

Product Description

The RF2186 is a high-power, high-efficiency linear amplifier IC targeting 3V handheld systems. The device is manufactured on an advanced Gallium Arsenide Hetero-junction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in 3V CDMA-2000 and W-CDMA handsets, spread-spectrum systems, and other applications in the 1850MHz to 2000MHz band. The device is self-contained with 50Ω input and the output can be easily matched to obtain optimum power, efficiency, and linearity characteristics over all recommended supply voltages.

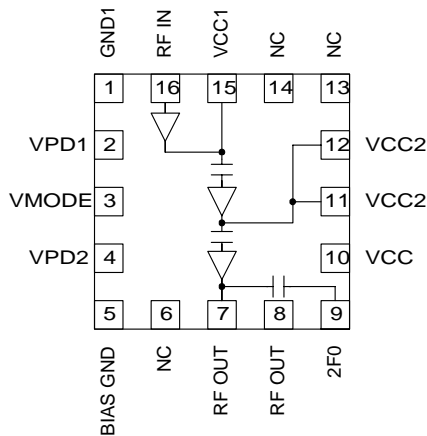


- NOTES:
- ▷ Shaded Pin is Lead 1.
 - ▷ Dimension applies to plated terminal and is measured 0.10 mm and 0.25 mm from terminal tip.
 - ▷ The terminal #1 identifier and terminal numbering conv shall conform to JEDEC 95-1 SPP-012. Details of terminal identifier are optional, but must be located within the so indicated. The identifier may be either a mold or mark feature.
 - 4 Pins 1 and 9 are fused.
 - 5 Package Warpage: 0.05 max.

Optimum Technology Matching® Applied

- Si BJT
- GaAs HBT
- GaAs MESFET
- Si Bi-CMOS
- SiGe HBT
- Si CMOS

Package Style: LCC, 16-Pin



Functional Block Diagram

Features

- Single 3V Supply
- 27dBm Linear Output Power
- 31dB Linear Gain
- 35% Linear Efficiency
- On-board Power Down Mode

Ordering Information

RF2186	3V W-CDMA Power 1900MHZ/ 3V Linear Power Amplifier
RF2186 PCBA	Fully Assembled Evaluation Board

RF Micro Devices, Inc. Tel (336) 664 1233
7625 Thorndike Road Fax (336) 664 0454
Greensboro, NC 27409, USA <http://www.rfmd.com>

Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage (RF off)	+8.0	V _{DC}
Supply Voltage (P _{OUT} ≤31dBm)	+5.0	V _{DC}
Mode Voltage (V _{MODE})	+3.0	V _{DC}
Control Voltage (V _{PD})	+3.0	V _{DC}
Input RF Power	+6	dBm
Operating Case Temperature	-30 to +100	°C
Storage Temperature	-30 to +150	°C



Caution! ESD sensitive device.

RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

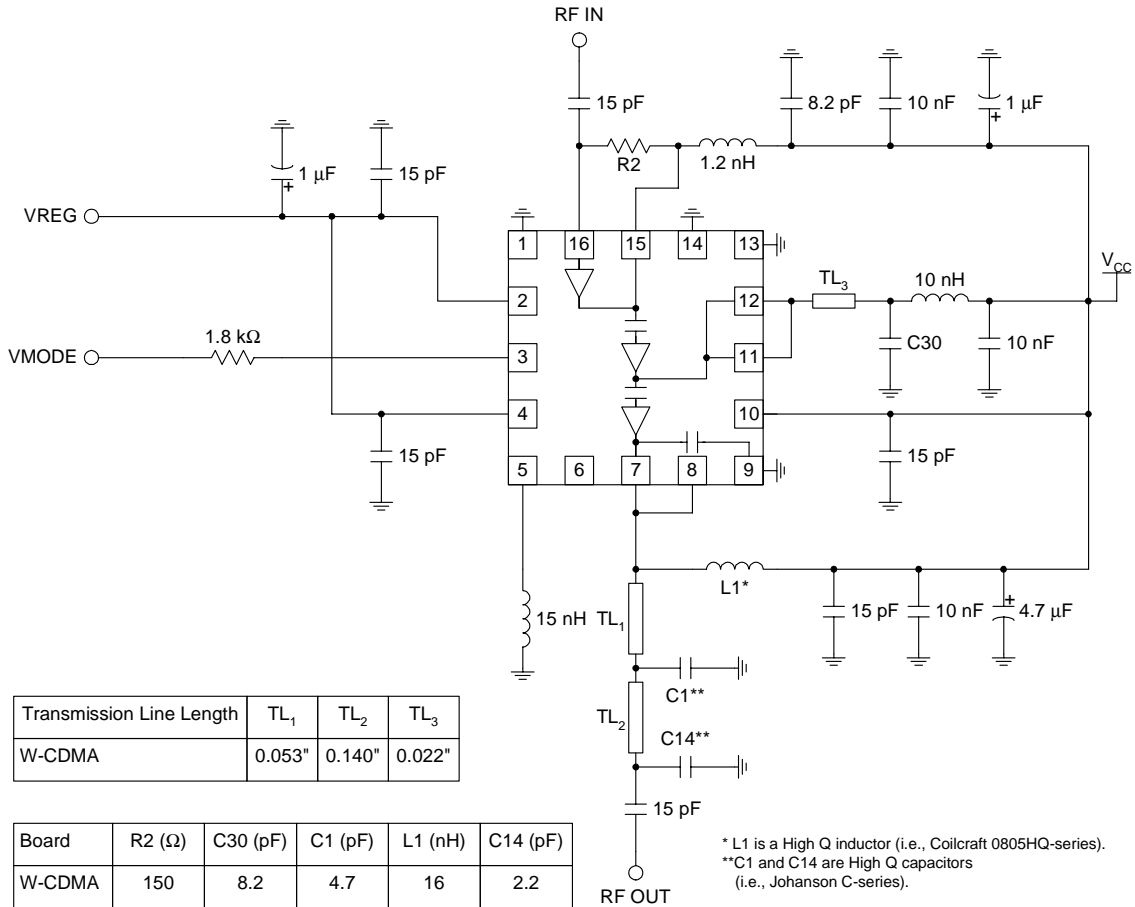
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Overall					T=-25°C, V _{CC} =3.4V, V _{REG} =2.8V, Freq=1920MHz to 1980MHz (unless otherwise specified)
Usable Frequency Range	1850		2000	MHz	
Typical Frequency Range		1850 to 1910 1920 to 1980		MHz	
Linear Gain	31	34		dB	Mode=Low
	28	31		dB	Mode=High
Second Harmonic (including second harmonic trap)		-35		dBc	
Third Harmonic		-40		dBc	
Fourth Harmonic		-45		dBc	
Maximum Linear Output Power (W-CDMA Modulation)	27			dBm	
Total Linear Efficiency	30	35		%	P _{OUT} =27dBm, V _{MODE} High
Adjacent Channel Power Rejection @ 5MHz		-40	-38	dBc	P _{OUT} =27dBm, W-CDMA Modulation 3G PP 3.2 03-00 DPCCH+1DPDCH
Adjacent Channel Power Rejection @ 10MHz		-50	-48	dBc	P _{OUT} =27dBm, W-CDMA Modulation 3G PP 3.2 03-00 DPCCH+1DPDCH
Noise Power		-137		dBm/Hz	P _{OUT} =+27dBm, Rx Band 2110MHz to 2170MHz
Maximum Linear Output Power (W-CDMA Modulation)		26		dBm	V _{CC} =3.0V
Total Linear Efficiency		34		%	
Input VSWR		< 2:1			
Output Load VSWR			5:1		No oscillations
Power Supply					
Power Supply Voltage	3.0	3.4	5.0	V	
Idle Current		120		mA	MODE = high
V _{PD} Current		13		mA	Total pins 2 and 4, V _{PD} = 2.8 V
Total Current (Power down)		10		µA	V _{PD} = low
V _{PD} "Low" Voltage		0	0.2	V	
V _{PD} "High" Voltage	2.7	2.8	2.9	V	
MODE "High" Voltage	2.5	2.8			
MODE "Low" Voltage		0	0.5		

Pin	Function	Description	Interface Schematic
1	GND1	Ground for first stage. For best performance, keep traces physically short and connect immediately to ground plane. This ground should be isolated from the backside ground contact.	See pin 16.
2	VPD1	Power Down control for first and second stages. When this pin is "low", all first and second stage circuits are shut off. When this pin is 2.8V, all first and second stage circuits operate normally. V_{PD1} requires a regulated 2.8V for the amplifier to operate properly over all specified temperature and voltage ranges. A dropping resistor from a higher regulated voltage may be used to provide the required 2.8V.	
3	VMODE	V_{MODE} adjusts the bias to the second and third stages. In normal operation and for maximum efficiency, V_{MODE} should be "high". In this mode the power and linearity will meet the published specifications. If additional linearity is desired, V_{MODE} may be pulled "low", however efficiency will decrease. If V_{MODE} is pulled "low", the output match will need to be adjusted for optimum performance.	
4	VPD2	Power Down control for third stage. When this pin is "low", all third stage circuits are shut off. When this pin is 2.8V, all third stage circuits operate normally. V_{PD} requires a regulated 2.8V for the amplifier to operate properly over all specified temperature and voltage ranges. A dropping resistor from a higher regulated voltage may be used to provide the required 2.8V. A 15pF high frequency bypass capacitor is recommended.	
5	BIAS GND	For best performance, keep traces physically short and connect to ground plane through a 15nH inductor. This ground should be isolated from the backside ground contact.	
6	NC	Not Connected.	
7	RF OUT	RF output and power supply for final stage. This is the unmatched collector output of the third stage. A DC block is required following the matching components. The biasing may be provided via a parallel L-C set for resonance at the operating frequency of 1920MHz to 1980MHz. It is important to select an inductor with very low DC resistance with a 1A current rating. Alternatively, shunt microstrip techniques are also applicable and provide very low DC resistance. Low frequency bypassing is required for stability.	
8	RF OUT	Same as pin 7.	See pin 7.
9	2FO	Second harmonic trap. Keep traces physically short and connect immediately to ground plane. This ground should be isolated from backside ground contact.	
10	VCC	Supply for bias reference and control circuits. High frequency bypassing may be necessary.	
11	VCC2	Power supply for second stage and interstage match. Pins 11 and 12 should be connected by a common trace where the pins contact the printed circuit board.	
12	VCC2	Same as pin 11.	
13	NC	Not Connected.	
14	NC	Not Connected.	
15	VCC1	Power supply for first stage and interstage match. V_{CC} should be fed through a 1.2nH inductor terminated with a 8.2pF capacitor on the supply side. The inductor should be as close to the pin as possible.	See pin 16.
16	RF IN	RF input. An external series capacitor is required as a DC block.	
Pkg Base	GND	Ground connection. The backside of the package should be soldered to a top side ground pad which is connected to the ground plane with multiple vias. The pad should have a short thermal path to the ground plane.	

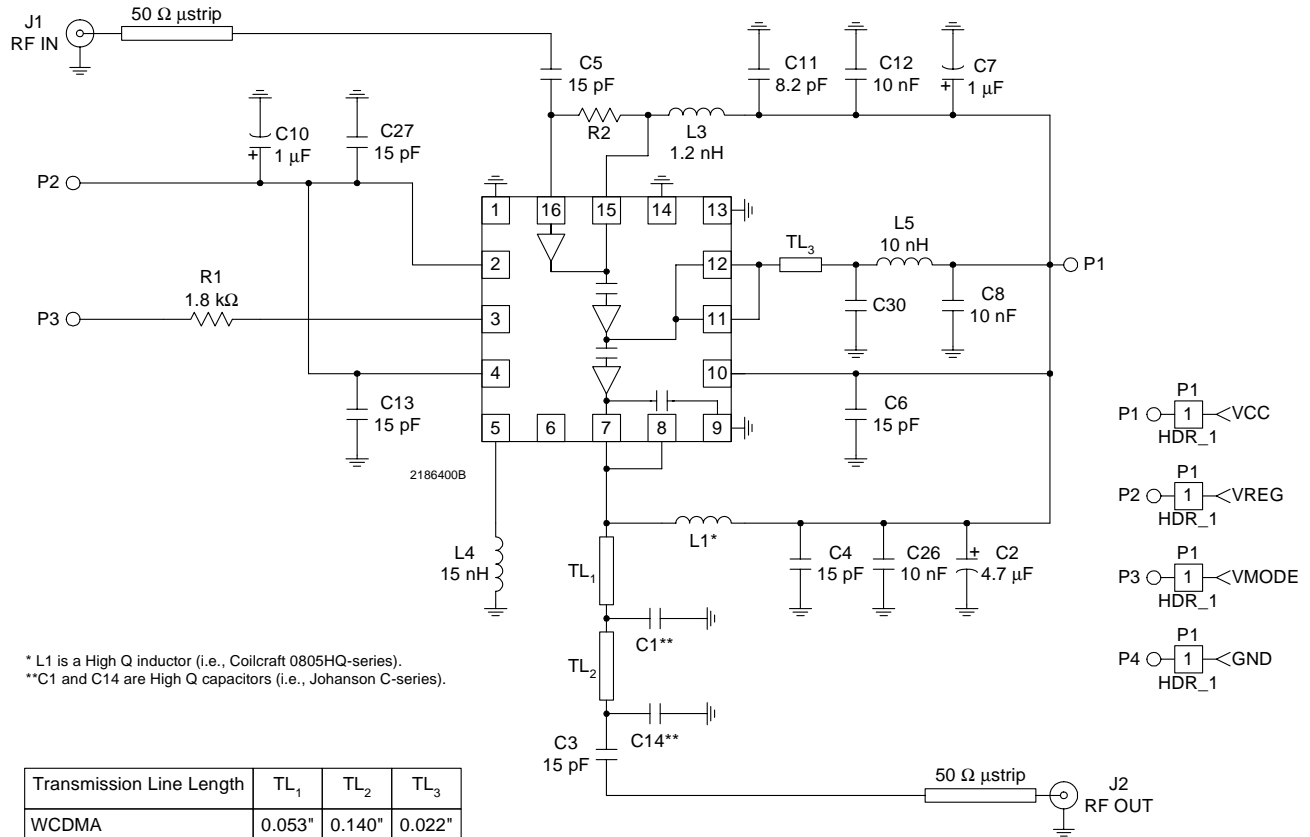
Application Schematic W-CDMA (1920MHz to 1980MHz)

2

POWER AMPLIFIERS



Evaluation Board Schematic W-CDMA (1920MHz to 1980MHz)



* L1 is a High Q inductor (i.e., Coilcraft 0805HQ-series).
**C1 and C14 are High Q capacitors (i.e., Johanson C-series).

Transmission Line Length	TL ₁	TL ₂	TL ₃
WCDMA	0.053"	0.140"	0.022"

Board	R2 (Ω)	C30 (pF)	C1 (pF)	L1 (nH)	C14 (pF)
WCDMA	150	8.2	4.7	16	2.2

Evaluation Board Layout
Board Size 2.0" x 2.0"

Board Thickness 0.028", Board Material FR-4, Multi-Layer, Ground Plane at 0.014

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POWER AMPLIFIERS

